

Appl. No. 10/820,856
Amendment dated: February 16, 2007
Reply to OA of: November 16, 2006

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1 (currently amended). An under bump metallization structure applicable to be disposed on bonding pads of a semiconductor wafer, wherein a passivation layer covers the wafer and exposes the bonding pads, the under bump metallization structure comprising:

- an adhesive layer formed on the bonding pads;
- a first barrier layer disposed on the adhesive layer;
- a wetting layer formed on the first barrier layer; and
- a second barrier layer disposed on the wetting layer, wherein a material of the second barrier comprises tin and copper and wherein the quantity of copper is larger than that of tin.

Claim 2(canceled).

3(original). The structure of claim 1, wherein the first barrier layer is a nickel-vanadium layer.

4(original). The structure of claim 1, wherein the wetting layer is a copper layer.

Claims 5 and 6(canceled).

7(original). The structure of claim 1, wherein the thickness of the second barrier layer is ranged from about 50 μm to about 80 μm .

Claims 8-19(canceled).